Preferred Device

Power MOSFET 200 mA, 50 V

N-Channel SOT-23

Typical applications are DC-DC converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Low Threshold Voltage (V_{GS(th)}: 0.5 V-1.5 V) Makes it Ideal for Low Voltage Applications
- Miniature SOT-23 Surface Mount Package Saves Board Space
- Pb-Free Packages are Available

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	50	Vdc
Gate-to-Source Voltage - Continuous	V _{GS}	± 20	Vdc
Drain Current - Continuous @ $T_A = 25^{\circ}C$ - Pulsed Drain Current $(t_p \le 10 \mu s)$	I _D I _{DM}	200 800	mA
Total Power Dissipation @ T _A = 25°C	P _D	225	mW
Operating and Storage Temperature Range	T _J , T _{stg}	– 55 to 150	°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	TL	260	°C

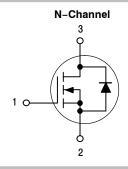
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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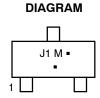
http://onsemi.com

200 mA, 50 V $R_{DS(on)} = 3.5 Ω$





SOT-23 CASE 318 STYLE 21



MARKING

J1 = Device Code M = Date Code* = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BSS138LT1	SOT-23	3000 Tape & Reel
BSS138LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
BSS138LT3	SOT-23	10,000 Tape & Reel
BSS138LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

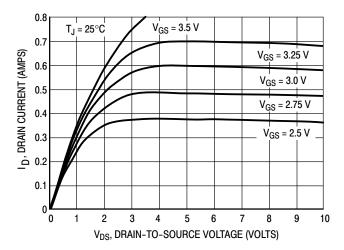
Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic			Min	Тур	Max	Unit	
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 250 μAdc)		V _{(BR)DSS}	50	_	_	Vdc	
Zero Gate Voltage Drain Current (V _{DS} = 25 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 50 Vdc, V _{GS} = 0 Vdc)		I _{DSS}	- -	- -	0.1 0.5	μAdc	
Gate-Source Leakage Current (V _{GS} = ± 20 Vdc, V _{DS} = 0 Vdc)		I _{GSS}	-	-	±0.1	μ Adc	
ON CHARACTERISTICS (Note 1)							
Gate-Source Threshold Voltage (V _{DS} = V _{GS} , I _D = 1.0 mAdc)	V _{GS(th)}	0.5	_	1.5	Vdc		
Static Drain-to-Source On-Resistance $ (V_{GS}=2.75~Vdc,~I_D<200~mAdc,~T_A=-40^{\circ}C~to~+85^{\circ}C) \\ (V_{GS}=5.0~Vdc,~I_D=200~mAdc) $		r _{DS(on)}	_ _ _	5.6 -	10 3.5	Ω	
Forward Transconductance (V _{DS} = 25 Vdc, I _D = 200 mAdc, f = 1.0 kHz)		9fs	100	_	_	mmhos	
DYNAMIC CHARACTERISTICS		•		•	•	•	
Input Capacitance	$(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ MHz})$	C _{iss}	-	40	50	pF	
Output Capacitance	(V _{DS} = 25 Vdc, V _{GS} = 0, f = 1 MHz)	C _{oss}	-	12	25	1	
Transfer Capacitance	$(V_{DG} = 25 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ MHz})$	C _{rss}	-	3.5	5.0		
SWITCHING CHARACTERISTICS (N	ote 2)	•	•	•	•		
Turn-On Delay Time	(V _{DD} = 30 Vdc, I _D = 0.2 Adc,)	t _{d(on)}	-	_	20	ns	
Turn-Off Delay Time	(VDD = 30 Vdc, ID = 0.2 Adc,)	t _{d(off)}	-	_	20]	

Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.

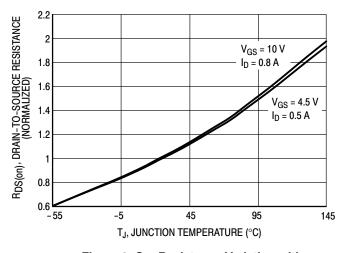
TYPICAL ELECTRICAL CHARACTERISTICS



0.9 25°C $V_{DS} = 10 V$ 0.8 -55°C ID, DRAIN CURRENT (AMPS) 0.7 150°C 0.6 0.5 0.4 0.3 0.2 0.1 0.5 4.5 VGS, GATE-TO-SOURCE VOLTAGE (VOLTS)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



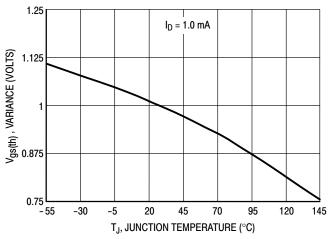
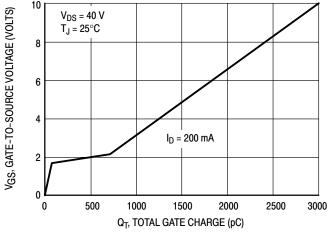


Figure 3. On–Resistance Variation with Temperature

Figure 4. Threshold Voltage Variation with Temperature



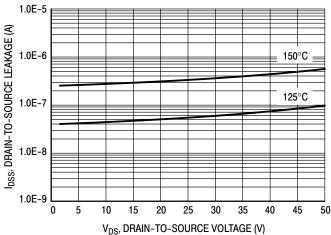
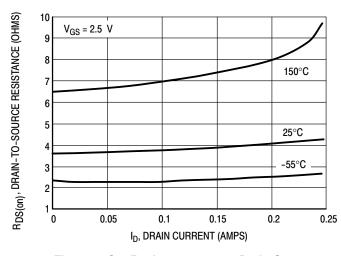


Figure 5. Gate Charge

Figure 6. IDSS

TYPICAL ELECTRICAL CHARACTERISTICS



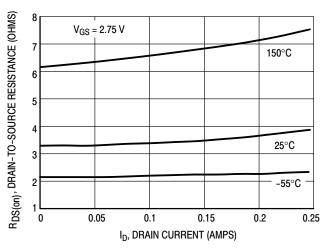
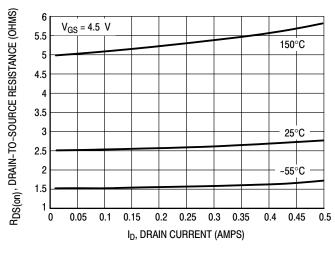


Figure 7. On-Resistance versus Drain Current

Figure 8. On-Resistance versus Drain Current



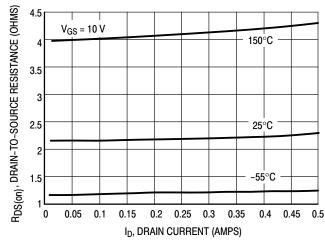
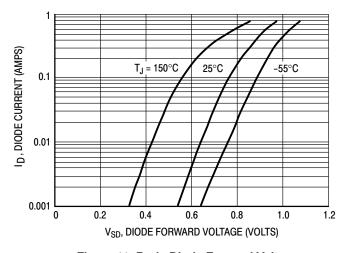


Figure 9. On-Resistance versus Drain Current

Figure 10. On-Resistance versus Drain Current



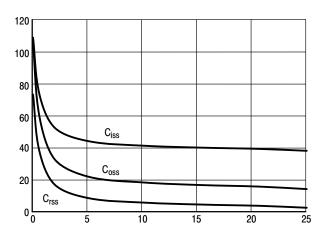
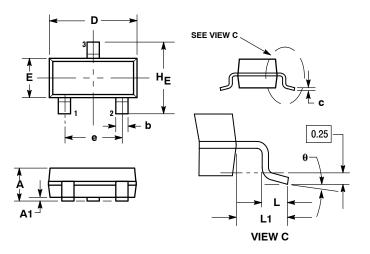


Figure 11. Body Diode Forward Voltage

Figure 12. Capacitance

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**



NOTES:

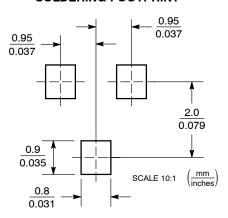
- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- B. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 21: PIN 1. GATE 2. SOUR

- - SOURCE DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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